

# Yuri Shreter

## List of Publications by Year in descending order

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63  
papers

1,165  
citations

430874

18  
h-index

395702

33  
g-index

63  
all docs

63  
docs citations

63  
times ranked

1015  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of the joule heating on the quantum efficiency and choice of thermal conditions for high-power blue InGaN/GaN LEDs. <i>Semiconductors</i> , 2006, 40, 605-610.	0.5	213
2	Stacking Faults as Quantum Wells for Excitons in Wurtzite GaN. <i>Physica Status Solidi A</i> , 1997, 164, 141-144.	1.7	98
3	Defect-related tunneling mechanism of efficiency droop in III-nitride light-emitting diodes. <i>Applied Physics Letters</i> , 2010, 96, 133502.	3.3	84
4	Cathodoluminescence and Transmission Electron Microscopy Study of the Influence of Crystal Defects on Optical Transitions in GaN. <i>Physica Status Solidi A</i> , 1999, 171, 325-339.	1.7	83
5	Strain and microstructure variation in grains of CVD diamond film. <i>Diamond and Related Materials</i> , 1995, 4, 1222-1234.	3.9	47
6	Luminescence Related to Stacking Faults in Heteroepitaxially Grown Wurtzite GaN. <i>Materials Research Society Symposia Proceedings</i> , 1997, 468, 293.	0.1	42
7	Light Emitting Diode with Charge Asymmetric Resonance Tunneling. <i>Physica Status Solidi A</i> , 2000, 180, 121-126.	1.7	32
8	Efficiency droop and incomplete carrier localization in InGaN/GaN quantum well light-emitting diodes. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	31
9	Tunnel-recombination currents and electroluminescence efficiency in InGaN/GaN LEDs. <i>Semiconductors</i> , 2005, 39, 594-599.	0.5	27
10	Nature of V-Shaped Defects in GaN. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JE14.	1.5	25
11	A Classification of the Dislocation-Related Photoluminescence in Silicon. <i>Physica Status Solidi (B): Basic Research</i> , 1992, 172, 53-63.	1.5	23
12	Dislocation Luminescence in Wurtzite GaN. <i>Materials Research Society Symposia Proceedings</i> , 1996, 449, 683.	0.1	23
13	Laser slicing: A thin film lift-off method for GaN-on-GaN technology. <i>Results in Physics</i> , 2019, 13, 102233.	4.1	23
14	Mechanism of the GaN LED efficiency falloff with increasing current. <i>Semiconductors</i> , 2010, 44, 794-800.	0.5	22
15	Photoluminescence and Electronic Structure of Dislocations in Si Crystals. <i>Materials Science Forum</i> , 1992, 83-87, 1321-1326.	0.3	21
16	Dislocation-related absorption and photoluminescence in deformed n-ZnSe crystals. <i>Journal of Crystal Growth</i> , 1996, 159, 883-888.	1.5	21
17	Influence of Poisson's ratio uncertainty on calculations of the bowing parameter for strained InGaN layers. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2001, 6, 1.	1.0	21
18	Metastable Transitions in the Mass Spectrum of Iron Pentacarbonyl. <i>The Journal of Physical Chemistry</i> , 1966, 70, 2057-2058.	2.9	19

#	ARTICLE	IF	CITATIONS
19	Influence of cathode material and SiCl <sub>4</sub> gas on inductively coupled plasma etching of AlGaIn layers with Cl <sub>2</sub> -Ar plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2336-2341.	2.1	18
20	Two modes of HVPE growth of GaN and related macrodefects. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 468-471.	0.8	18
21	Optical properties of dislocations in silicon crystals. Physica Status Solidi A, 1993, 138, 681-686.	1.7	17
22	Efficiency droop in GaN LEDs at high current densities: Tunneling leakage currents and incomplete lateral carrier localization in InGaIn/GaN quantum wells. Semiconductors, 2014, 48, 1079-1087.	0.5	17
23	Nonuniformity of carrier injection and the degradation of blue LEDs. Semiconductors, 2006, 40, 118-123.	0.5	14
24	Increase in the Shockley-Read-Hall recombination rate in InGaIn/GaN QWs as the main mechanism of the efficiency droop in LEDs at high injection levels. Semiconductors, 2015, 49, 1665-1670.	0.5	14
25	Deformation-induced defect levels in ZnSe crystals. Semiconductor Science and Technology, 1999, 14, 430-434.	2.0	13
26	Tunnel injection and power efficiency of InGaIn/GaN light-emitting diodes. Semiconductors, 2013, 47, 127-134.	0.5	13
27	Degradation and transient currents in III-nitride LEDs. , 2003, , .		11
28	Measurement of the absorption coefficient for light laterally propagating in light-emitting diode structures with In <sub>0.2</sub> Ga <sub>0.8</sub> N/GaN quantum wells. Semiconductors, 2008, 42, 1342-1345.	0.5	10
29	Effect of localized tail states in InGaIn on the efficiency droop in GaN light-emitting diodes with increasing current density. Semiconductors, 2012, 46, 1032-1039.	0.5	10
30	Hopping conductivity and dielectric relaxation in Schottky barriers on GaN. Semiconductors, 2017, 51, 1186-1193.	0.5	10
31	Luminescence of CdSnP <sub>2</sub> doped with different impurities. Physica Status Solidi A, 1971, 8, 387-391.	1.7	9
32	Non-destructive identification of end-of-range damage in ion-implanted and annealed silicon. Applied Surface Science, 1993, 63, 227-231.	6.1	9
33	Anisotropic polarization of dislocation-related luminescence in thin ZnSe films. Physica B: Condensed Matter, 1999, 273-274, 895-897.	2.7	9
34	Quantum efficiency and formation of the emission line in light-emitting diodes based on InGaIn/GaN quantum well structures. Semiconductors, 2007, 41, 87-93.	0.5	9
35	Instability of an elastically compressed silicon surface under etching. Physics of the Solid State, 1999, 41, 1295-1297.	0.6	8
36	ICP etching of III-nitride based laser structure with Cl <sub>2</sub> -Ar plasma assisted by Si coverplate material. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 687-692.	2.1	8

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37	Determination of the coefficient of light attenuation in thin layers of light-emitting diodes. Semiconductors, 2006, 40, 375-378.	0.5	8
38	Optical properties of blue light-emitting diodes in the InGaN/GaN system at high current densities. Semiconductors, 2008, 42, 1355-1361.	0.5	8
39	Thick GaN Films Grown on Patterned Sapphire Substrates. ECS Transactions, 2011, 35, 91-97.	0.5	8
40	Hopping transport in the space-charge region of p-n structures with InGaN/GaN QWs as a source of excess 1/f noise and efficiency droop in LEDs. Semiconductors, 2015, 49, 827-835.	0.5	7
41	Effect of Deep Centers on Charge-Carrier Confinement in InGaN/GaN Quantum Wells and on LED Efficiency. Semiconductors, 2018, 52, 934-941.	0.5	7
42	Magnetic Resonance of Conduction Electrons in Dislocated Germanium. Physica Status Solidi (B): Basic Research, 1992, 172, 287-294.	1.5	6
43	Excitons Bound to Stacking Faults in Wurtzite GaN. Materials Research Society Symposia Proceedings, 1997, 468, 179.	0.1	6
44	Efficiency droop in GaN LEDs at high injection levels: Role of hydrogen. Semiconductors, 2016, 50, 1369-1376.	0.5	6
45	The effects of interface states on the capacitance and electroluminescence efficiency of InGaN/GaN light-emitting diodes. Semiconductors, 2005, 39, 795-799.	0.5	5
46	The effect of the transformation of point defects under Joule heating on efficiency of LEDs with InGaN/GaN quantum wells. Technical Physics Letters, 2016, 42, 1099-1102.	0.7	5
47	Electric-Dipole Spin Resonance of Electrons on $60^\circ$ -Dislocations in Plastically Deformed $n\text{-}\xi\text{-Ge}$ and $n\text{-}\xi\text{-Si}$ . Physica Status Solidi A, 1993, 137, 603-610.	1.7	4
48	Amorphous carbon buffer layers for separating free gallium nitride films. Technical Physics Letters, 2016, 42, 1076-1078.	0.7	4
49	On the laser detachment of n-GaN films from substrates, based on the strong absorption of IR light by free charge carriers in n <sup>+</sup> -GaN substrates. Semiconductors, 2016, 50, 699-704.	0.5	4
50	Effect of the electric field on the intensity and spectrum of emission from InGaN/GaN quantum wells. Semiconductors, 2009, 43, 1499-1505.	0.5	3
51	Scratch-Related Effects on Silicon Surface. Materials Science Forum, 1995, 196-201, 1231-1236.	0.3	2
52	Effect of Plastic Deformation on the Luminescence of ZnSe Crystals. Solid State Phenomena, 1998, 63-64, 207-214.	0.3	2
53	III-Nitride Unipolar Light Emitting Devices. Physica Status Solidi A, 2000, 180, 307-313.	1.7	2
54	Effect of Growth Parameters on Stress in HVPE GaN Films. ECS Transactions, 2011, 35, 73-81.	0.5	2

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55	On the laser lift-off of lightly doped micrometer-thick n-GaN films from substrates via the absorption of IR radiation in sapphire. <i>Semiconductors</i> , 2017, 51, 115-121.	0.5	2
56	Dislocation-Related Absorption, Photoluminescence and Birefringence in Deformed n-ZnSe Crystals. <i>Solid State Phenomena</i> , 1996, 51-52, 93-98.	0.3	1
57	Kinetic mechanism of surface instability evolution during etching, corrosion, and growth of elastically stressed solids. <i>Physics of the Solid State</i> , 2001, 43, 169-175.	0.6	1
58	Luminescence spectra of ternary compounds of Tl3BX4 type. <i>Physica Status Solidi A</i> , 1972, 9, K127-K128.	1.7	0
59	High-voltage optoelectronic voltage converter using a cascade of tunnel-coupled p +i-n + diodes. <i>Technical Physics Letters</i> , 1998, 24, 857-859.	0.7	0
60	Misfit dislocations and radiative efficiency of InxGa1-xN/GaN quantum wells. <i>Applied Surface Science</i> , 2000, 166, 300-303.	6.1	0
61	<title>III-nitride efficient LEDs</title>. , 2001, , .		0
62	Light scattering by dislocations in group-III nitrides. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 2880-2887.	1.8	0
63	Evolution of stress distributions and morphology of CVD diamond films. <i>Acta Crystallographica Section A: Foundations and Advances</i> , 1996, 52, C370-C370.	0.3	0